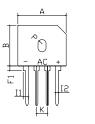


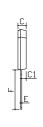
## GBU8A-GBU8M Silicon Bridge Rectifiers



#### **FEATURES**

- Rating to 1000V PRV
- Surge overload rating to 200 Amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded
- plastic technique results in inexpensive product
- Lead solderable per MIL-STD-202 method 208
- Glass passivated junctions





GBU								
Dim	Min	Max						
Α	22.00	22.40						
В	18.40	18.80						
С	3.40	3.95						
C1	2.50	3.00						
E	0.40	0.60						
F	17.00min							
F1	1.70	2.30						
I1	2.30	2.60						
12	0.95	1.25						
K	4.70	5.30						
Р	P R1.9ypical							
All Dimensions in mm								

**Maximum Ratings** (@TA = 25°C unless otherwise specified)

Maximum Pratings (@171 25 o unicos otriciwise spesifica)									
Characteristic	Symbol	GBU8A	GBU8B	GBU8D	GBU8G	GBU8J	GBU8K	GBU8M	UNITS
Maximum recurrent peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Maximum average forward Output	I <sub>F(AV)</sub>	20							Α
current @Tc=100 $^{\circ}$ C		=(AV) 8.0							A
Peak forward surge current									
8.3ms single half-sine-wav	I <sub>FSM</sub>	I <sub>FSM</sub> 200							Α
superimposed on rated load									
I²t Rating for fusing @Tj=25 C	I²t				166				A²S

### **Thermal Characteristics**

Characteristic	Symbol	GBU8A	GBU8B	GBU8D	GBU8G	GBU8J	GBU8K	GBU8M	UNITS
Typical junctionp capacitance per element(note 3)	CJ		211 94					pF	
Typical thermal resistance (note2) (note1)	$R_{\scriptscriptstyle{\theta JC}}$	2.2 1.6					°C/W		
Operating junction temperature range	TJ	- 55 + 150					°C		
Storage temperature range	T <sub>STG</sub>	- 55 + 150				$^{\circ}$ C			

#### Electrical Characteristics (@TA = 25°C unless otherwise specified)

Characteristic	Symbol	GBU8A	GBU8B	GBU8D	GBU8G	GBU8J	GBU8K	GBU8M	UNITS
Maximum instantaneous forward voltage @4.0A @8.0A	$V_{F}$				1.0 1.1				<b>&gt;</b>
Maximum reverse current @T <sub>A</sub> =25°C	ı				5.0				μА
at rated DC blocking voltage @T <sub>A</sub> =125℃	I <sub>R</sub>				0.5				mA

NOTE: 1. Unit case mounted on 3.2x3.2x0.12" thick (6.2x8.2x0.3cm) Al. Plate

- 2. Units mounted in free air, no heat sink on P.C.B., 0.5x0.5"(12x12mm) copper pads, 0.375"(9.5mm) lead length.
- 3. Measured at 1.0 MHz and applied reverse voltage of 4.0 volts.



#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

**Fig.1 Forward Current Derating Curve** 

12 AVERAGE FORWARD CURRENT (A) 8 **RESISTER OR** INDUCTIVE LOAD WITH HEATSINK 120 0 20 40 60 80 100 140 160 CASE TEMPERATURE (°C)

**Fig.2 Typical Junction Capacitance** 

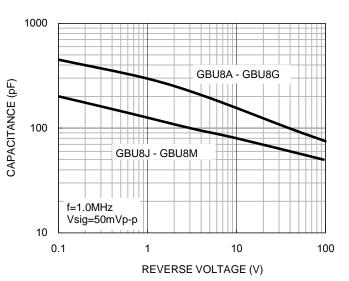


Fig.3 Typical Reverse Characteristics

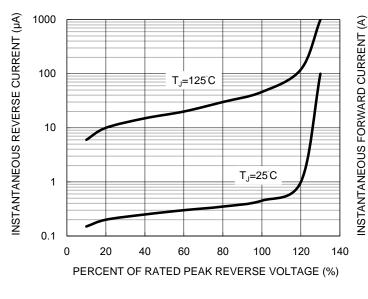
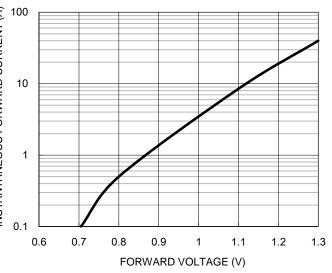


Fig.4 Typical Forward Characteristics





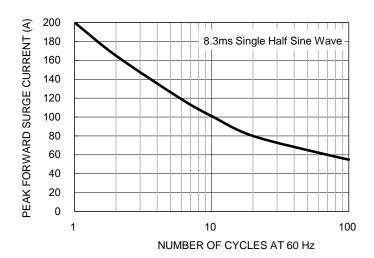
# GBU8A-GBU8M Silicon Bridge Rectifiers



#### **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)

Fig.5 Maximum Non-repetitive Forward Surge Current



Device	Package	Shipping
GBU8AGBU8M	GBU	500 Units/Box